

High Performance Schottky Rectifier

2x40A/100V

FEATURES

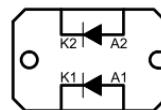
- 175°C T_J operation
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- 2 independent Schottky diodes in 1 package
- Designed and qualified for industrial level
- International standard package SOT-227
- Low I_{RM} values
- UL approved file E320098 

DESCRIPTION

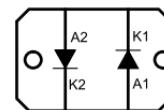
The NST80S100E Schottky rectifier module has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature.



CIRCUIT CONFIGURATION



Parallel
NST80S100



Anti-Parallel
NST80S100-A

TYPICAL APPLICATIONS

- High current switching mode power supplies (SMPS)
- Freewheeling diode in low voltage converters
- Reverse battery protection.

PRODUCT SUMMARY

$I_{F(AV)}$	40Ax2
V_R	100V

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNIT
$I_{F(AV)}$	Rectangular waveform, per diode	40	A
V_{RRM}		100	V
I_{FSM}	$t_p = 10 \text{ ms (50Hz), half-sine wave, } T_J=25^\circ\text{C}$	500	A
V_F	40 Apk, $T_J = 125^\circ\text{C}$	0.70	V
T_J	Range	-55 to 175	°C

VOLTAGE RATINGS

PARAMETER	SYMBOL	VALUES	UNIT
Maximum DC reverse voltage	V_R	100	V
Maximum working peak reverse voltage	V_{RWM}		

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNIT		
Maximum average forward current per leg	$I_{F(AV)}$	50% duty cycle at $T_C = 110^\circ\text{C}$, rectangular waveform			40	A		
Maximum peak one cycle non-repetitive surge current	I_{FSM}	10 ms sine	Following any rated load condition and with rated V_{RRM} applied		500			
Non-repetitive avalanche energy	E_{AS}	$T_J = 25^\circ\text{C}$, $I_{AS} = 10\text{A}$, $L = 0.1\text{mH}$			5	mJ		
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 μs $f = 10 \text{ KHz}$, $V_A = 1.5 \times V_R$ typical			1.0	A		

ELECTRICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNIT		
Maximum forward voltage drop per leg	$V_{FM}^{(1)}$	40A	$T_J = 25^\circ\text{C}$		0.87	V		
		80A			1.15			
		40A	$T_J = 125^\circ\text{C}$		0.70			
		80A			0.90			
Maximum reverse leakage current per leg	$I_{RM}^{(1)}$	$T_J = 25^\circ\text{C}$	$V_R = \text{Rated } V_R$		20	μA		
		$T_J = 125^\circ\text{C}$			10	mA		
Maximum junction capacitance per leg	C_T	$V_R = 5 \text{ V}_{\text{DC}}$ (test signal range 100 kHz to 1 MHz) 25°C			800	pF		
Typical series inductance per leg	L_S	From top of terminal hole to mounting plane			7	nH		
Maximum voltage rate of change	dV/dt	Rated V_R			5000	$\text{V}/\mu\text{s}$		
Maximum RMS insulation voltage	V_{INS}	50/60Hz, $I_{INS} < 1\text{mA}$			2500 (1 min) 3000 (1 s)	V		

Note

(1) Pulse width < 500 μs , duty cycle < 2%

THERMAL-MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum junction and storage temperature range	T_J, T_{Stg}	-55	-	175	$^\circ\text{C}$
Thermal resistance, junction to case	R_{thJC}	-	-	1.10	$^\circ\text{C}/\text{W}$
Thermal resistance, case to heatsink	R_{thCS}	-	0.10	-	
Weight		-	30 (1.06)	-	g(oz.)
Mounting torque, $\pm 10\%$	to heatsink, M4 busbar, M4	-	1.1 (9.7)	-	$\text{N}\cdot\text{m}$ ($\text{lbf}\cdot\text{in}$)
		-	1.1 (9.7)	-	
Case style		JEDEC SOT-227 module (insulated)			

Ordering Information Table

Device code	N	ST	80	S	100	-	A
	(1)	(2)	(3)	(4)	(5)		(6)

- [1] - Nell's high power module
- [2] - Package indicator, "ST" for SOT-227
- [3] - Maximum average forward current, 80 = 80A (40Ax2)
- [4] - S = Schottky family
- [5] - Voltage rating (100 = 100V)
- [6] - Circuit configuration, A for Anti-Parallel type
Blank for Parallel type

Fig.1 Maximum forward voltage drop characteristics

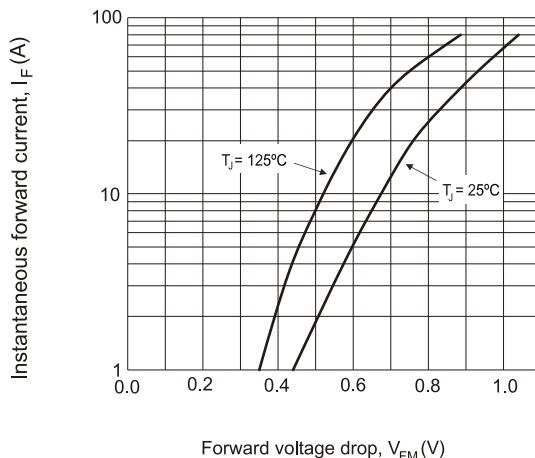


Fig.2 Typical values of reverse current vs. reverse voltage

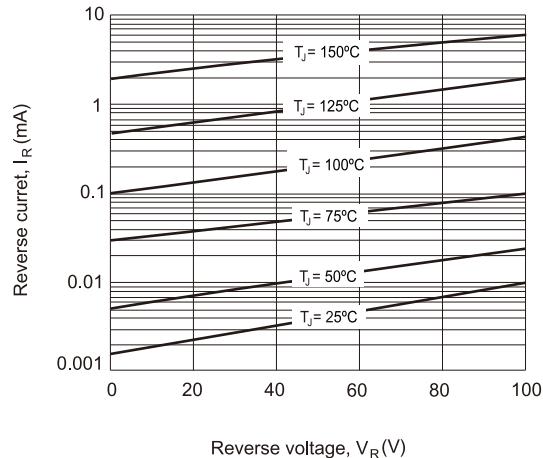


Fig.3 Maximum thermal impedance $R_{th(j-c)}$ characteristics

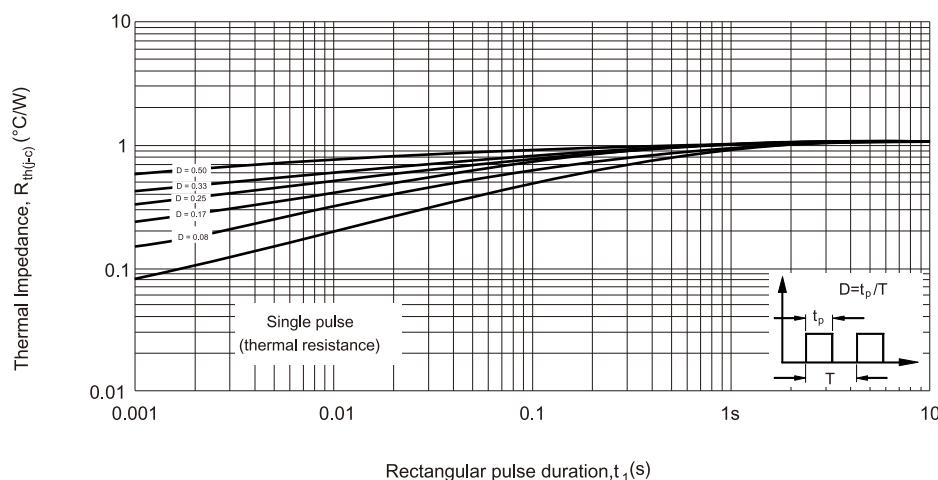
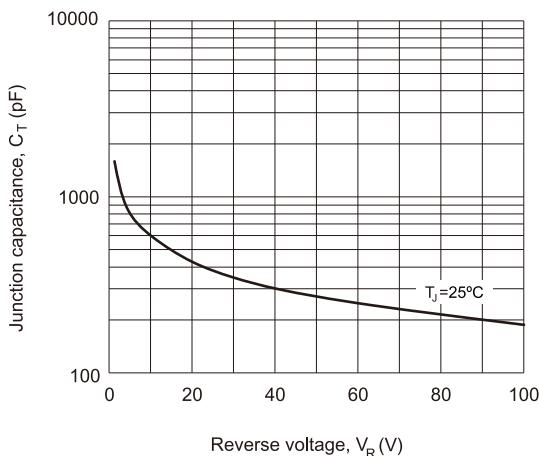
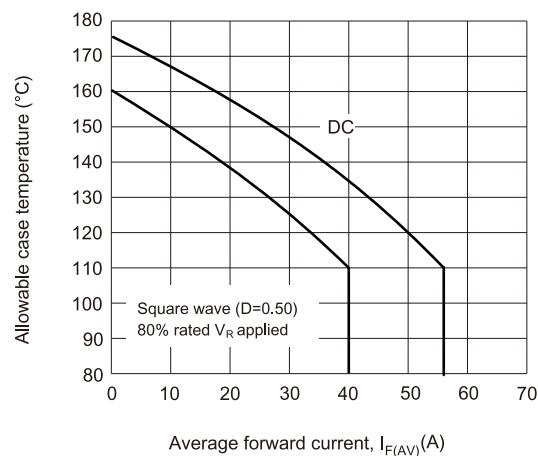
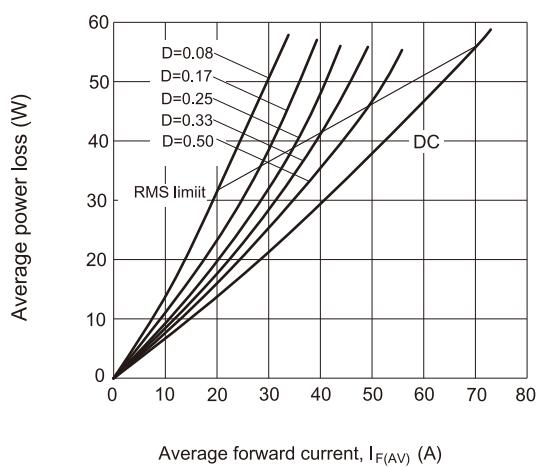
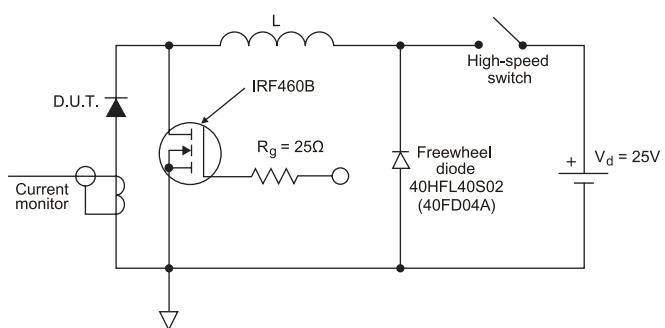
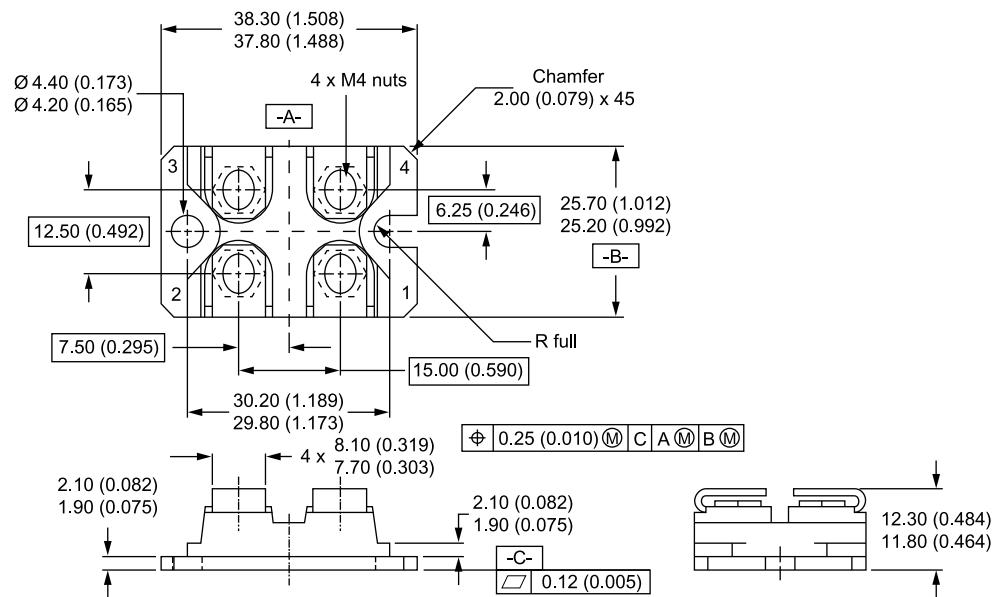


Fig.4 Typical junction capacitance vs. reverse voltage

Fig.5 Maximum allowable case temperature vs. Average forward current

Fig.6 Forward power loss characteristics

Fig.7 Unclamped Inductive test circuit

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{d\text{REV}}) \times R_{thJC}$;
 $P_d = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)})/D \text{ (see fig.6)}$
 $P_{d\text{REV}} = \text{Inverse power loss} = V_{R1} \times I_R (1-D); I_R \text{ at } V_{R1} = \text{rated } V_R$

SOT-227



All dimensions in millimeters (inches)

Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter